

Amendments to the Title:

Please delete the Title of the Application and replace it with the following title: SILICON
BUFFERED SHALLOW TRENCH ISOLATION.

Amendments to the Specification:

Please amend the specification as follows:

Please replace paragraph number [0054] with the following rewritten paragraph:

[0054] In FIGURE 7, a conformal layer **62** is formed in the trench associated with aperture **60** in a step **108** of process **100** by selective epitaxial growth. In one embodiment, layer **62** is a semiconductor or metal layer that can be formed at a low temperature (e.g., below approximately 600°C). Layer **62** is preferably a layer that can be oxidized to form an insulative material such as an oxide liner. Most preferably, layer **62** is a 50-200Å thick silicon layer deposited by CVD at a temperature of 500-600°C. Layer **62** is deposited in accordance with step **108** of process **100** (FIGURE 9).